

**Inchange Semiconductor**

**Product Specification**

**Silicon PNP Power Transistors**

**2SB1161**

**DESCRIPTION**

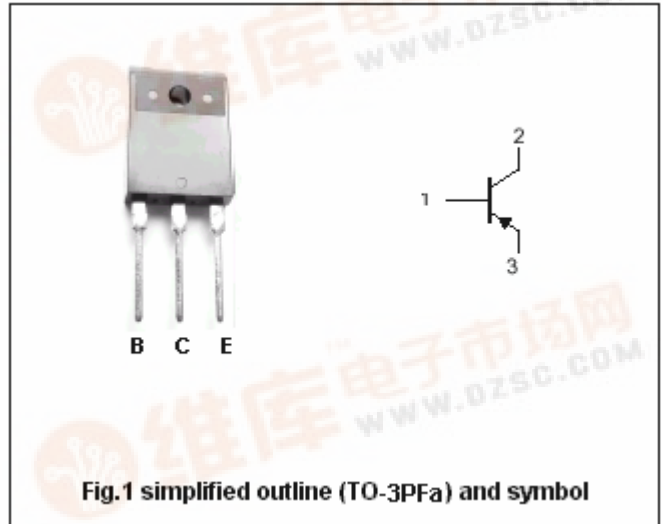
- With TO-3PFa package
- Complement to type 2SD1716
- High  $f_T$
- Wide area of safe operation

**APPLICATIONS**

- For high power amplifier applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



**Absolute maximum ratings(Ta=25 )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-160	V
$V_{CEO}$	Collector-emitter voltage	Open base	-160	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-12	A
$I_{CP}$	Collector current-peak		-20	A
$P_C$	Collector power dissipation	$T_C=25$	120	W
		$T_a=25$	3	
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

## Silicon PNP Power Transistors

## 2SB1161

## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-8A ; I <sub>B</sub> =-0.8A			-2.0	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =-8A ; V <sub>CE</sub> =-5V			-1.8	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-160V; I <sub>E</sub> =0			-50	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-3V; I <sub>C</sub> =0			-50	μ A
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-20mA ; V <sub>CE</sub> =-5V	20			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-5V	60		200	
h <sub>FE-3</sub>	DC current gain	I <sub>C</sub> =-8A ; V <sub>CE</sub> =-5V	20			
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =-10V; f=1MHz		420		pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.5A ; V <sub>CE</sub> =-5V		20		MHz

◆ h<sub>FE-2</sub> classifications

Q	S	P
60-120	80-160	100-200

